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July 20, 1999

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N.W.H.: tener  
8/14/99

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

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JUL 30 1999

Fr: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

TECHNOLOGY CENTER 2800

Subject:

Serial No. 09/325,951 ✓ 06/04/99 ✓

M.H. Chiang, J.Y. Lee, J.M. Huang ✓

METHOD FOR FORMING HIGH PURITY  
SILICON OXIDE FIELD OXIDE ISOLATION  
REGION ✓

Grp. Art Unit: 2812

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

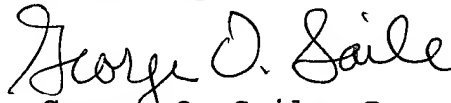
The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 5,151,381 to Liu et al., "Method for Local  
Oxidation of Silicon Employing Two Oxidation Steps", discloses  
a method for forming field isolation silicon oxide layers which  
reduces or eliminates localized defects known as ribbons.

U.S. Patent 5,554,560 to Hsue et al., "Method for Forming a Planar Field Oxide (FOX) on Substrates for Integrated Circuit", discloses a method for forming planar silicon oxide field oxide (FOX) isolation layers with improved resistance to formation of localized stringer defects.

U.S. Patent 5,686,344 to Lee, "Device Isolation Method for Semiconductor Device", discloses a method for forming silicon oxide dielectric isolation regions within a silicon substrate in both the device isolation and well regions separating different polarities of silicon.

Sincerely,

A handwritten signature in cursive script that reads "George O. Saile". The signature is written in dark ink and is positioned above the printed name.

George O. Saile, Reg. No. 19572